

## Product Overview

### MJW21196: Bipolar Transistor, NPN, 250 V, 16 A

For complete documentation, see the data sheet.

The MJW21196 NPN Bipolar Complementary Audio Power Transistor utilizes Perforated Emitter technology and is specifically designed for high power audio output, disk head positioners and linear applications.

### Features

- Total Harmonic Distortion Characterized
- High DC Current Gain  $-h_{FE} = 20 \text{ Min @ } I_C = 8 \text{ Adc}$
- Excellent Gain Linearity
- High SOA: 2.25 A, 80 V, 1 Second
- Pb-Free Packages are Available

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	$I_C$ Continuous (A)	$V_{CE(sus)}$ Min (V)	$h_{FE}$ Min	$h_{FE}$ Max	$P_{TM}$ Max (W)	$f_T$ Min (MHz)	Package Type
MJW21196G	2	Pb-free Halide free non AEC-Q and PPAP	Active	NPN	16	250	20	80	200	4	TO-247-3

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

Created on: 1/20/2021